N-Channel Enhancement Mode Field Effect Transistor

Product Summary

ð V_{DS} 100V

Electrical Characteristics (T_j=25 unless otherwise noted)

	Symbol				

Typical Performance Characteristics

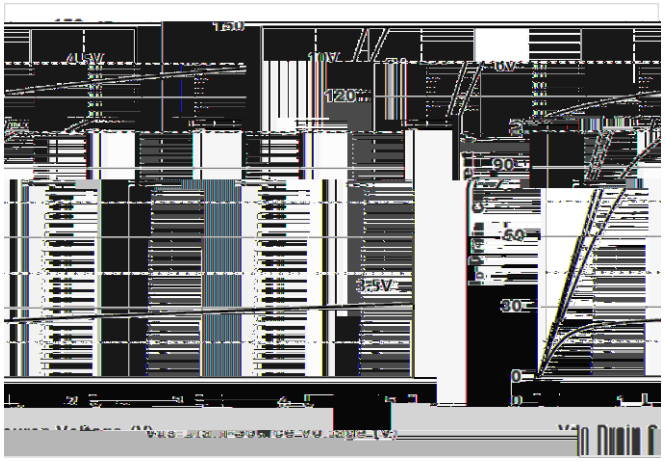

Figure1. Output Characteristics

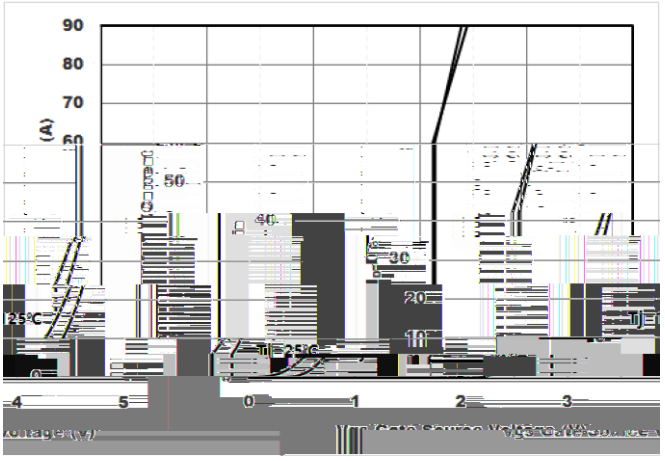

Figure2. Transfer Characteristics

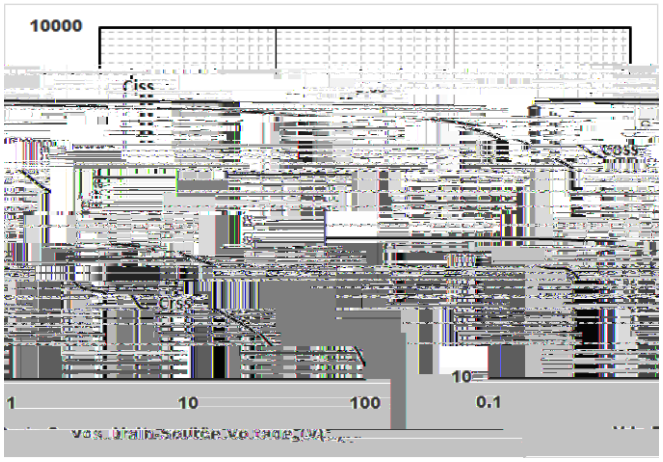

Figure3. Capacitance Characteristics

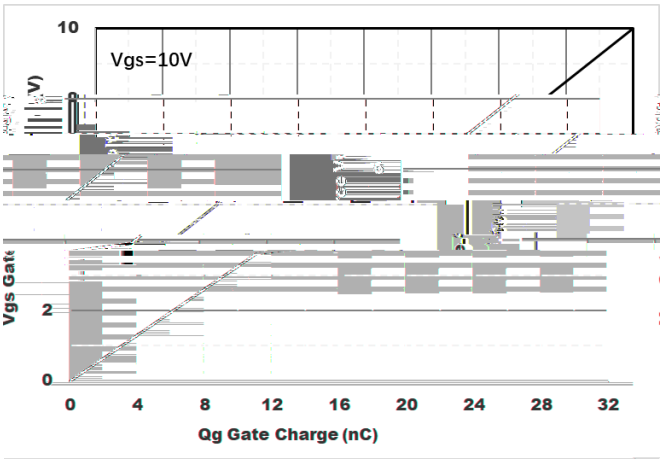

Figure4. Gate Charge

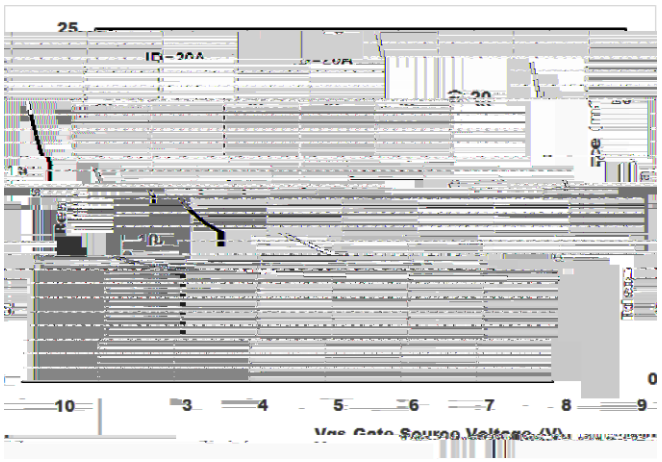

Figure5. On-Resistance vs. Drain Current and Gate Voltage

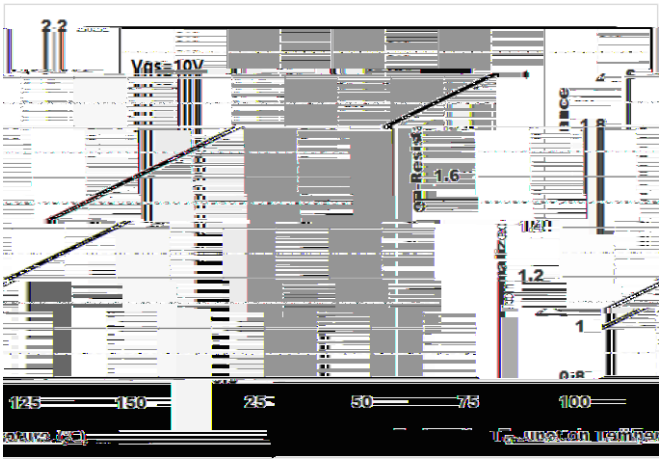

Figure6. Normalized On-Resistance

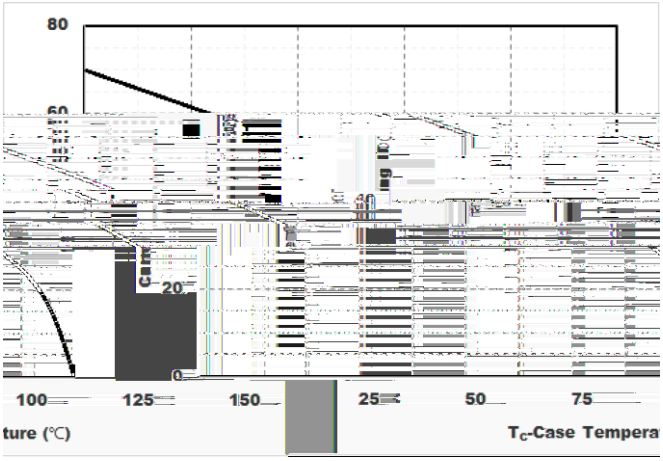

Figure7. Drain current

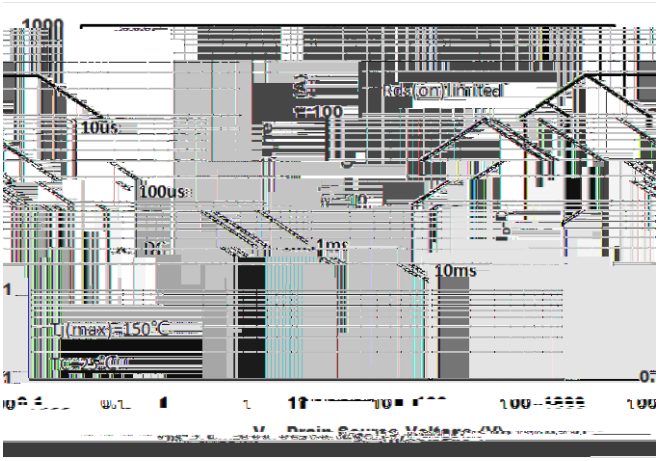

Figure8. Safe Operation Area

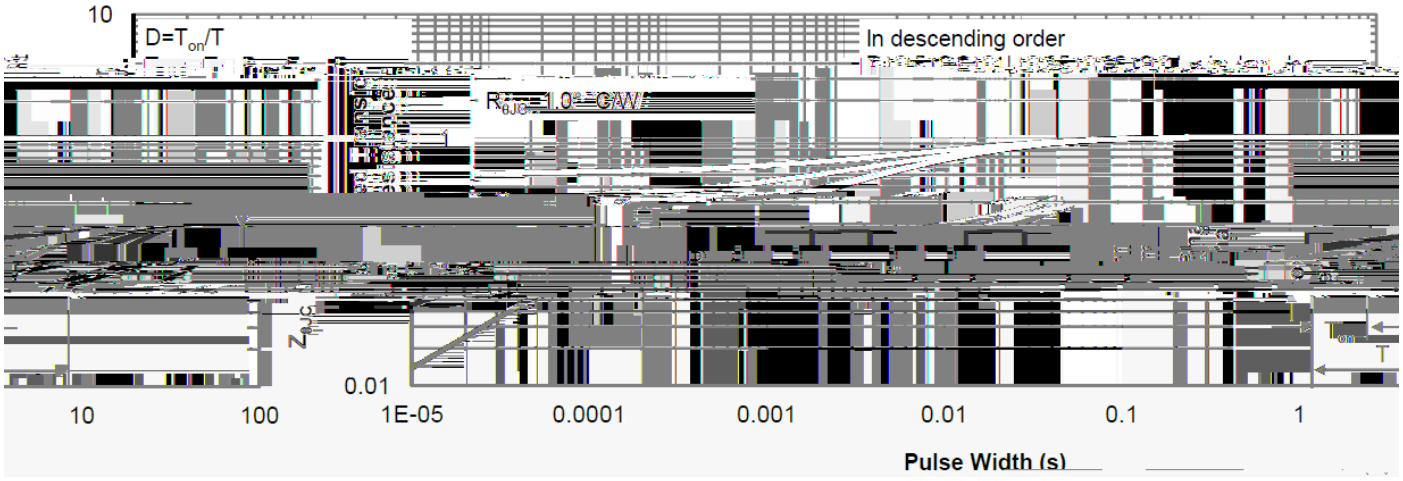

Figure9. Normalized Maximum Transient thermal impedance

y TO-220AB-C Package information

NOTE:

Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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